

Electronic Supplementary Information (ESI) for

Carrier mobilities and band alignments of inorganic perovskites of CsBX₃

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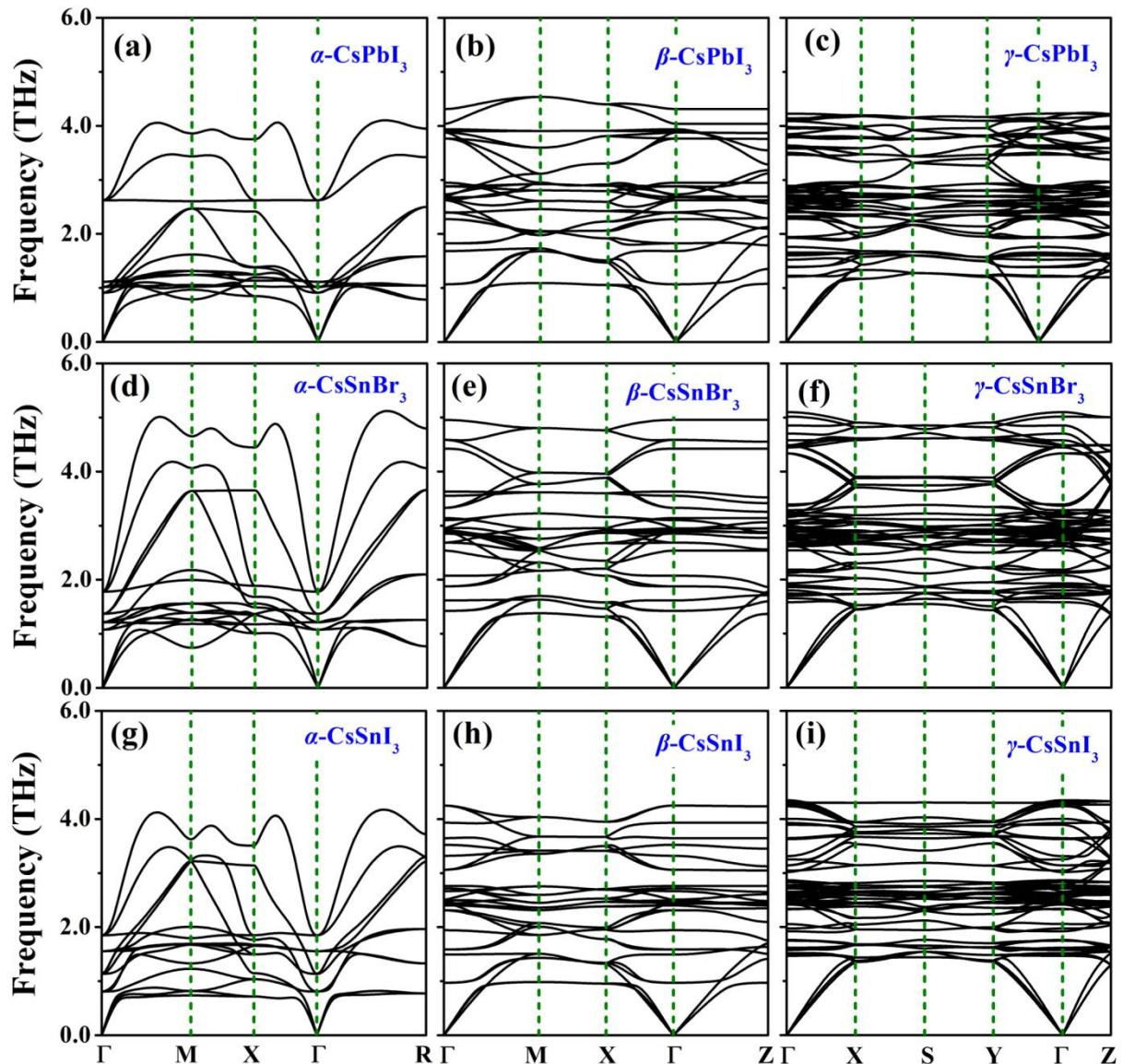


Fig. S1. Phonon spectra of CsPbI₃ in (a)-(c), CsSnBr₃ in (d)-(f), CsSnI₃ in (g)-(i) along the high symmetric directions.

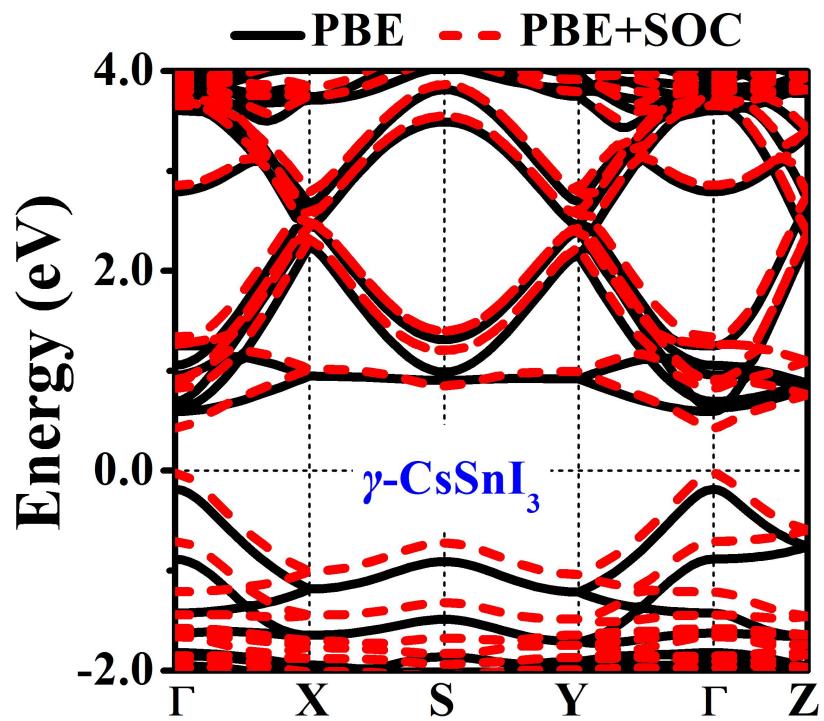


Fig. S2. Band structures of γ -CsSnI₃ based on GGA-PBE functional. The dashed lines and solid lines correspond to the band structures with and without considering the SOC effect, respectively.

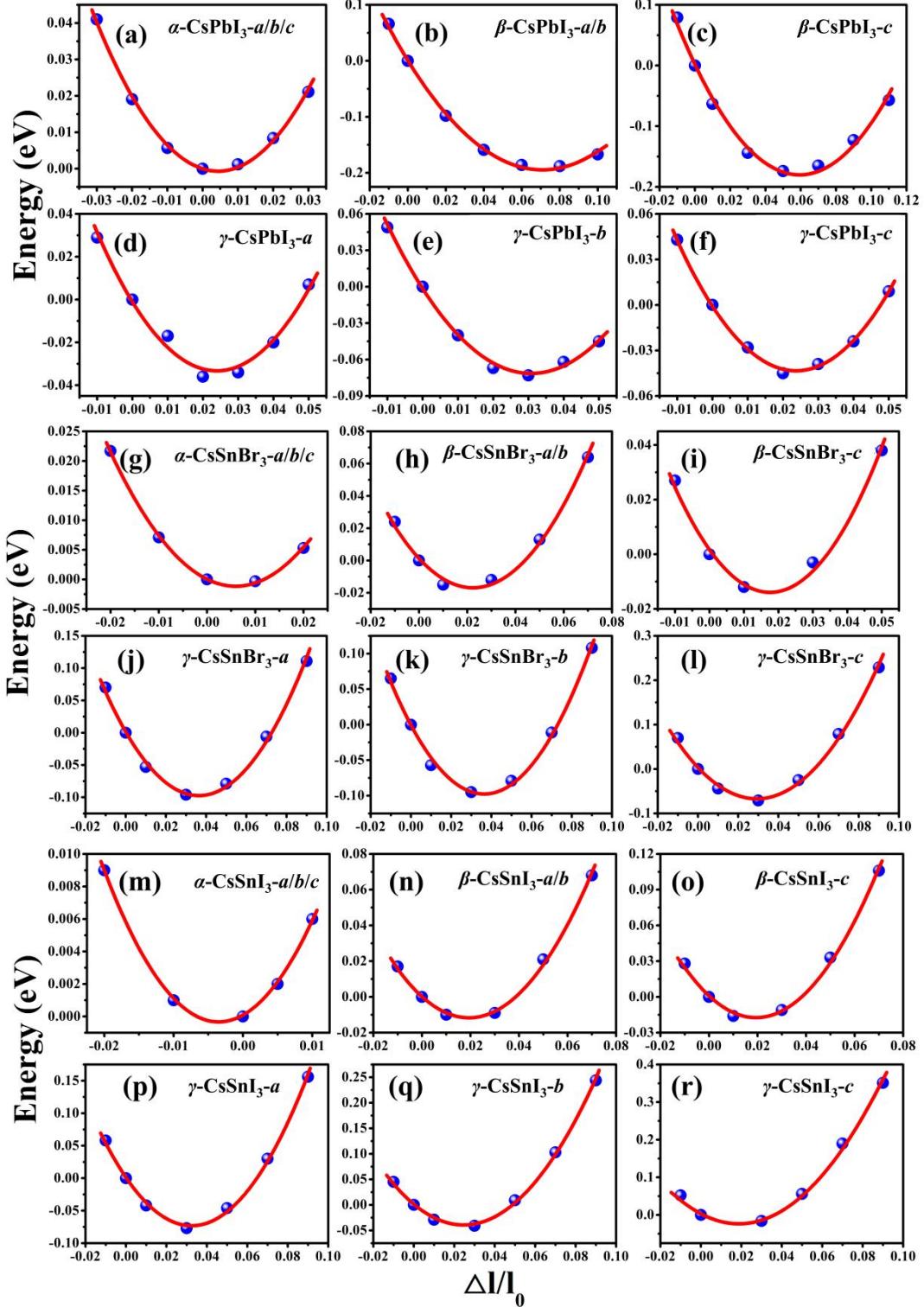


Fig. S3. The total energy difference of CsPbI₃ in (a-f), CsSnBr₃ in (g-l) and CsSnI₃ in (m-r) under different strain relative to the respective pristine system. The blue solid sphere corresponds to the total energy difference of the system under different strain, and the red line represent the quadratic fitting of total energy difference curve.

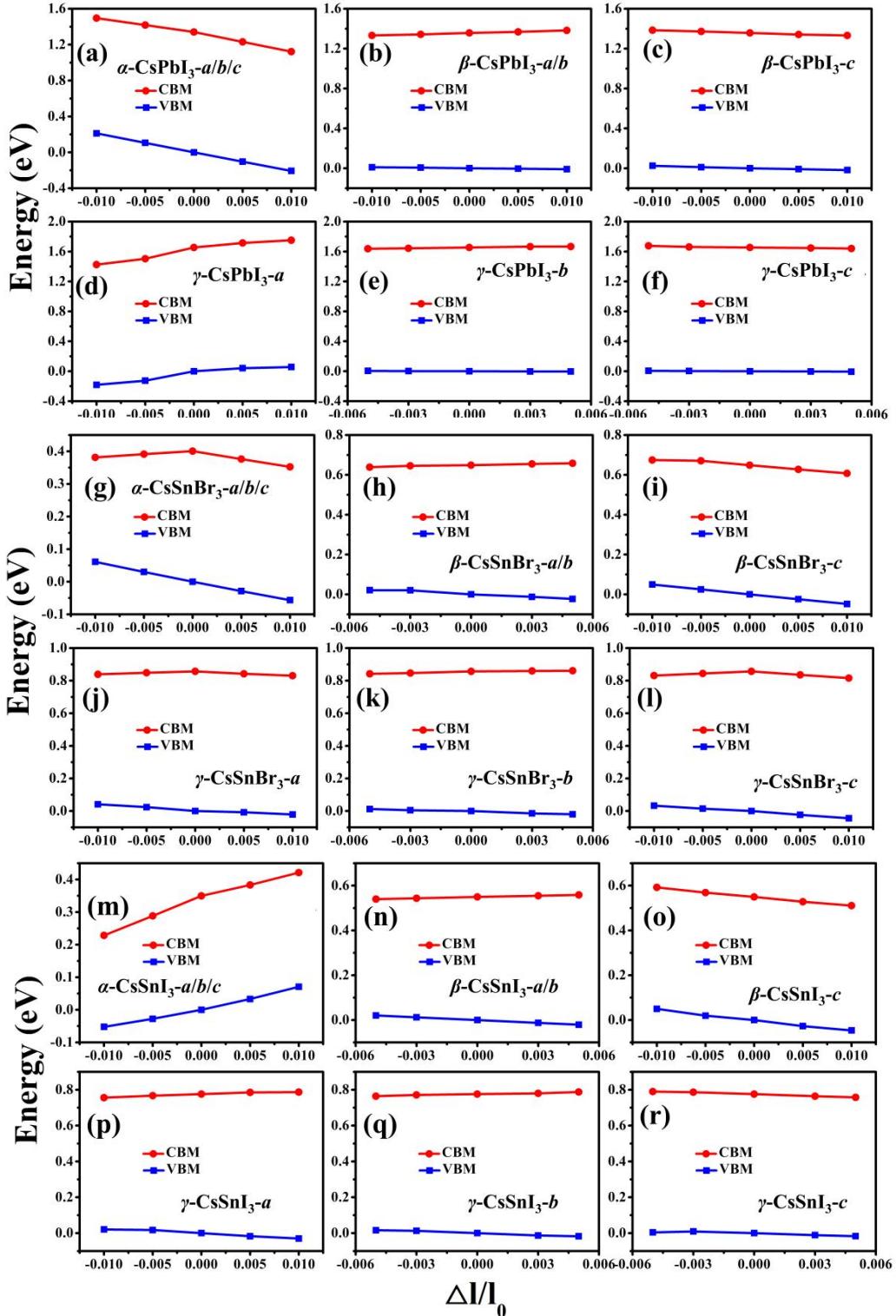


Fig. S4. The CBM and VBM difference of CsPbI₃ in (a-f), CsSnBr₃ in (g-l) and CsSnI₃ in (m-r) under different strain relative to the VBM of the respective pristine system. The deformation potentials can be obtained by linear fitting of the CBMs and VBMs. In particular, for CBMs in (g), (j), (l), the deformation potentials under tensile and compressive stresses are calculated separately, and the average values are taken.

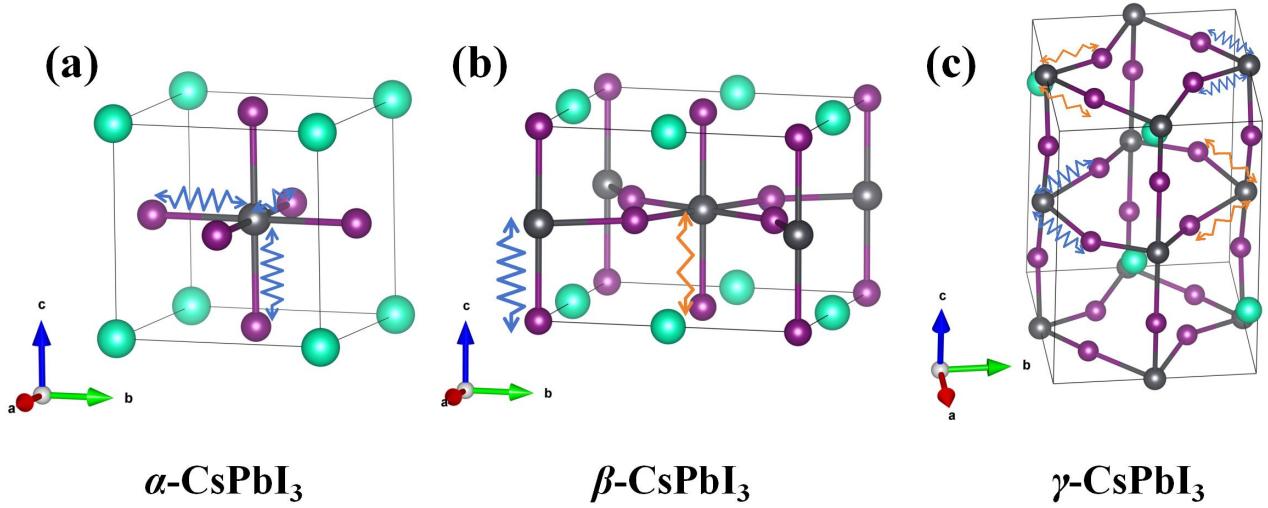


Fig. S5. Optical phonon vibration modes that play major roles in perovskites of α -, β - and γ - CsPbI_3 . Green balls represent Cs atoms, black balls represent Pb atoms, and purple balls represent I atoms. Blue and orange wavy lines represent opposite vibration directions.

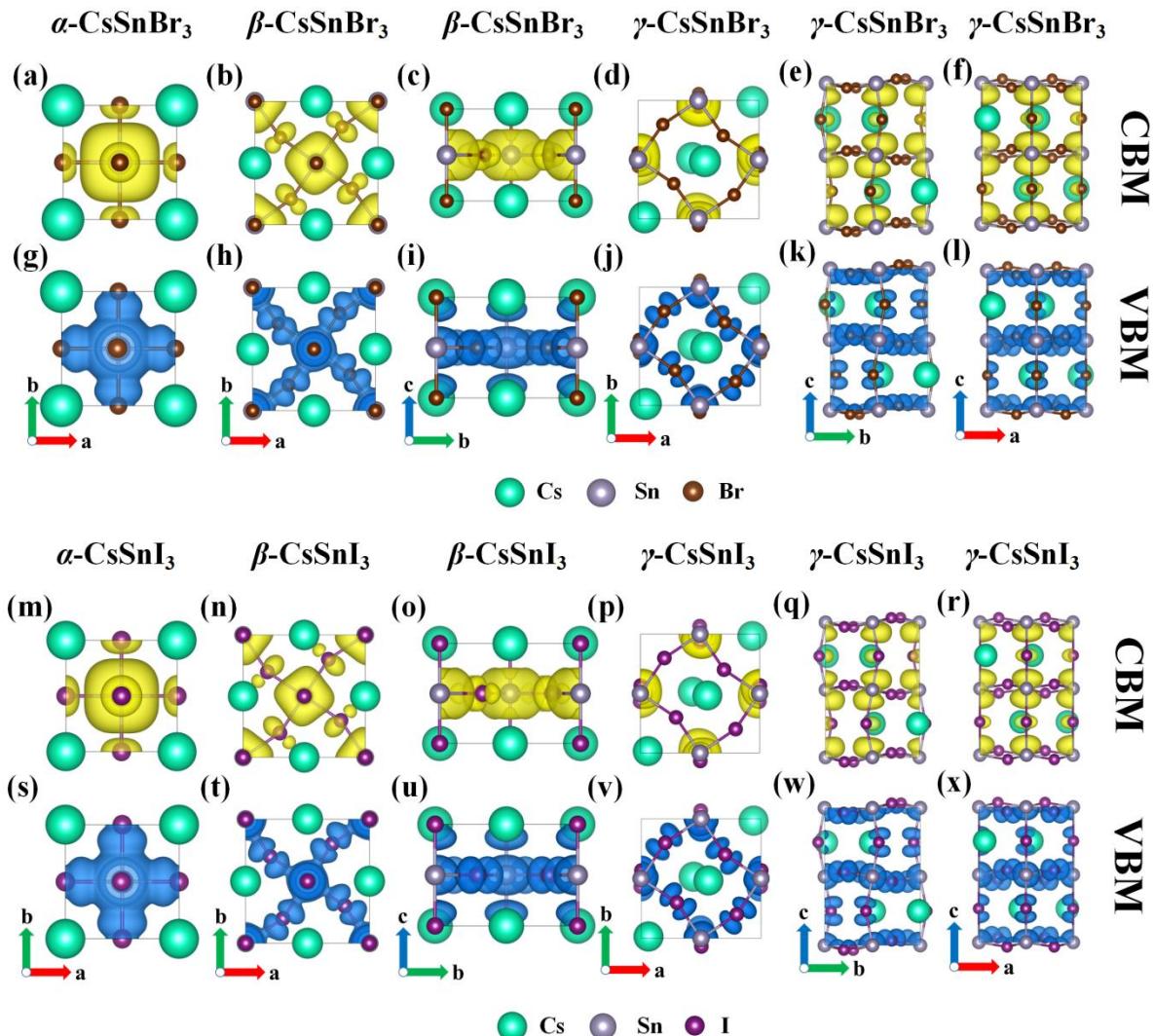


Fig. S6. Partial charge distribution plots of CsSnBr_3 in (a)-(l) and CsSnI_3 in (m)-(x). The isovalue is $0.01 \text{ e}/\text{\AA}^3$.

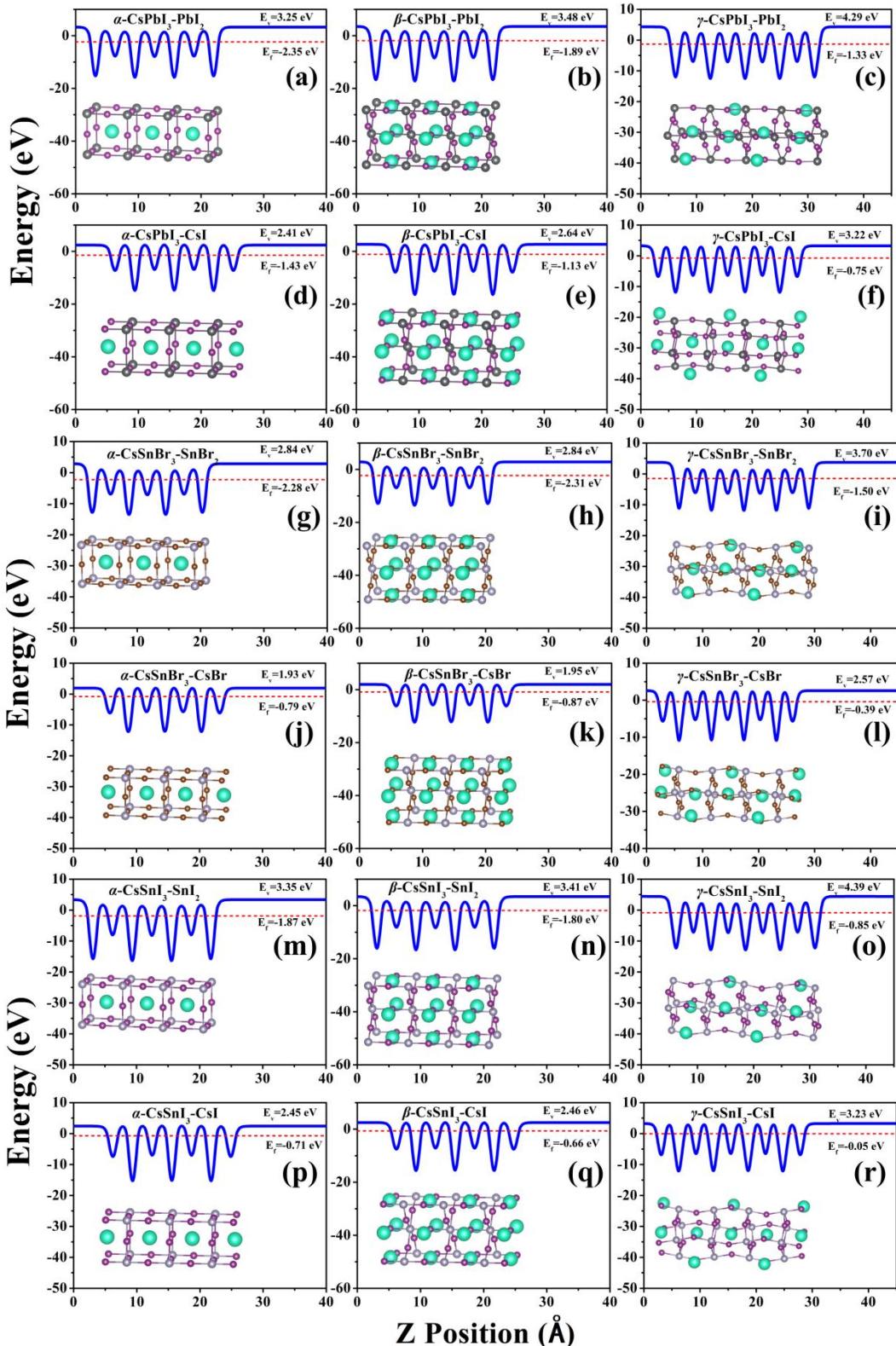


Fig. S7. The *ab* plane-averaged electrostatic potential of CsPbI_3 -(001) surfaces in (a-f), CsSnBr_3 -(001) surfaces in (g-l) and CsSnI_3 -(001) surfaces in (m-r) with BX_2 -terminated and CsX -terminated structures. The insets are the corresponding surface models, which corresponds to the electrostatic potential results.

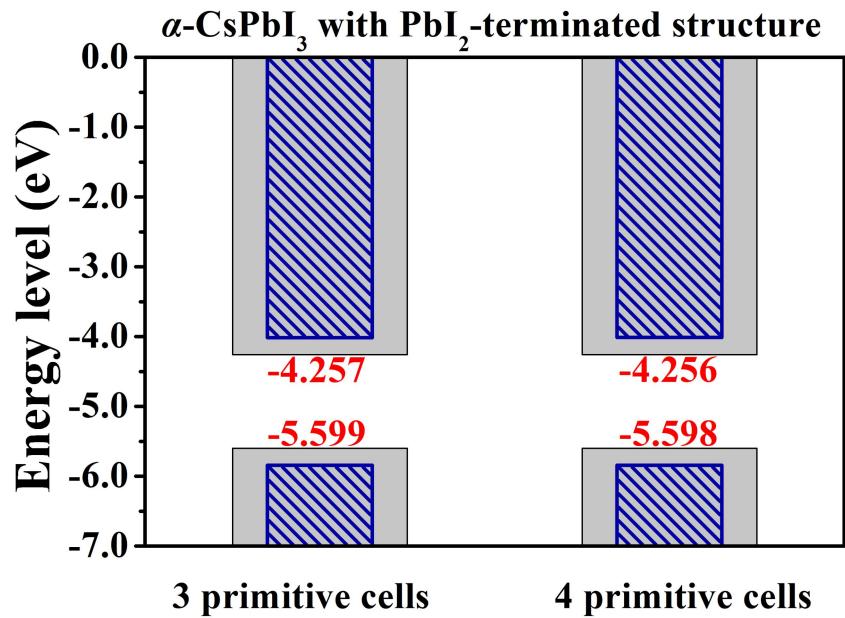


Fig. S8. The band-edge positions of $\alpha\text{-CsPbI}_3$ with three primitive cells and four primitive cells.

Table S1. Orbital components of CBM and VBM for CsBX₃.

| | | B-s | B-p _x | B-p _y | B-p _z | X-s | X-p _x | X-p _y | X-p _z |
|-------------------------------|---------------------|-------|------------------|------------------|------------------|-------|------------------|------------------|------------------|
| α -CsPbI ₃ | CBM(R) (%) | / | 26.70 | 26.70 | 26.70 | 11.86 | / | / | / |
| | VBM(R) (%) | 35.90 | / | / | / | / | 21.37 | 21.37 | 21.37 |
| β -CsPbI ₃ | CBM(Z) (%) | / | / | / | 79.65 | 12.04 | / | / | / |
| | VBM(Z) (%) | 34.92 | / | / | / | / | 21.93 | 21.93 | 21.07 |
| γ -CsPbI ₃ | CBM(Γ) (%) | / | 10.84 | 2.21 | 68.58 | 10.84 | / | / | / |
| | VBM(Γ) (%) | 33.09 | / | / | / | / | 24.71 | 19.56 | 22.65 |
| α -CsSnBr ₃ | CBM(R) (%) | / | 27.32 | 27.32 | 27.32 | 10.42 | / | / | / |
| | VBM(R) (%) | 43.61 | / | / | / | / | 18.80 | 18.80 | 18.80 |
| β -CsSnBr ₃ | CBM(Z) (%) | / | / | / | 82.80 | 10.40 | / | / | / |
| | VBM(Z) (%) | 42.14 | / | / | / | / | 18.88 | 18.88 | 19.98 |
| γ -CsSnBr ₃ | CBM(Γ) (%) | / | 0.79 | 5.56 | 75.20 | 9.52 | / | / | / |
| | VBM(Γ) (%) | 41.10 | / | / | / | / | 19.51 | 19.26 | 19.75 |
| α -CsSnI ₃ | CBM(R) (%) | / | 27.27 | 27.27 | 27.27 | 10.84 | / | / | / |
| | VBM(R) (%) | 43.99 | / | / | / | / | 18.72 | 18.72 | 18.72 |
| β -CsSnI ₃ | CBM(Z) (%) | / | / | / | 81.82 | 10.91 | / | / | / |
| | VBM(Z) (%) | 42.37 | / | / | / | / | 18.29 | 18.29 | 20.91 |
| γ -CsSnI ₃ | CBM(Γ) (%) | / | 0.81 | 7.33 | 71.28 | 9.78 | / | / | / |
| | VBM(Γ) (%) | 40.97 | / | / | / | / | 18.75 | 20.42 | 19.72 |

Table S2. CBM (E_C) and VBM (E_V) of CsBX_3 -(001) surfaces with BX_2 -terminated and CsX -terminated structures based on GGA-PBE and HSE functionals.

| | BX ₂ -terminated | | | | CsX-terminated | | | |
|--------------------------|-----------------------------|------------|------------|------------|----------------|------------|------------|------------|
| | GGA-PBE | | HSE | | GGA-PBE | | HSE | |
| | E_V (eV) | E_C (eV) | E_V (eV) | E_C (eV) | E_V (eV) | E_C (eV) | E_V (eV) | E_C (eV) |
| $\alpha\text{-CsPbI}_3$ | -5.60 | -4.26 | -5.85 | -4.02 | -3.84 | -2.50 | -4.09 | -2.26 |
| $\beta\text{-CsPbI}_3$ | -5.37 | -4.01 | -5.61 | -3.77 | -3.77 | -2.41 | -4.01 | -2.17 |
| $\gamma\text{-CsPbI}_3$ | -5.62 | -3.97 | -5.89 | -3.70 | -3.95 | -2.30 | -4.22 | -2.03 |
| $\alpha\text{-CsSnBr}_3$ | -5.12 | -4.72 | -5.34 | -4.51 | -2.72 | -2.32 | -2.94 | -2.11 |
| $\beta\text{-CsSnBr}_3$ | -5.15 | -4.50 | -5.37 | -4.29 | -2.82 | -2.17 | -3.04 | -1.96 |
| $\gamma\text{-CsSnBr}_3$ | -5.20 | -4.34 | -5.44 | -4.11 | -2.96 | -2.10 | -3.20 | -1.87 |
| $\alpha\text{-CsSnI}_3$ | -5.22 | -4.87 | -5.39 | -4.70 | -3.16 | -2.81 | -3.33 | -2.64 |
| $\beta\text{-CsSnI}_3$ | -5.21 | -4.66 | -5.38 | -4.50 | -3.12 | -2.57 | -3.29 | -2.41 |
| $\gamma\text{-CsSnI}_3$ | -5.24 | -4.46 | -5.44 | -4.27 | -3.28 | -2.50 | -3.48 | -2.31 |